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Sheet	1	of	1
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Application Number	10/050,570
Confirmation Number	7078
Filing Date	January 18, 2002
First Named Inventor	Kuniaki YAGI
Art Unit	1765
Examiner Name	SONG, MATTHEW
Attorney Docket Number	Q68148

U.S. PATENT DOCUMENTS

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁴
M)	.	BJÖRKETUN, L.-O. et al., "Interfacial Void Formation During Vapor Phase Growth of 3C-SiC on Si(0 0 1) and Si (1 1 1) Substrates Characterization by Transmission Electron Microscopy," Journal of Crystal Growth, December 1997, pp. 379-388, Vol. 182, No. 3-4, North-Holland Publishing Co., Amsterdam, NL.	
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